

FIG. 1

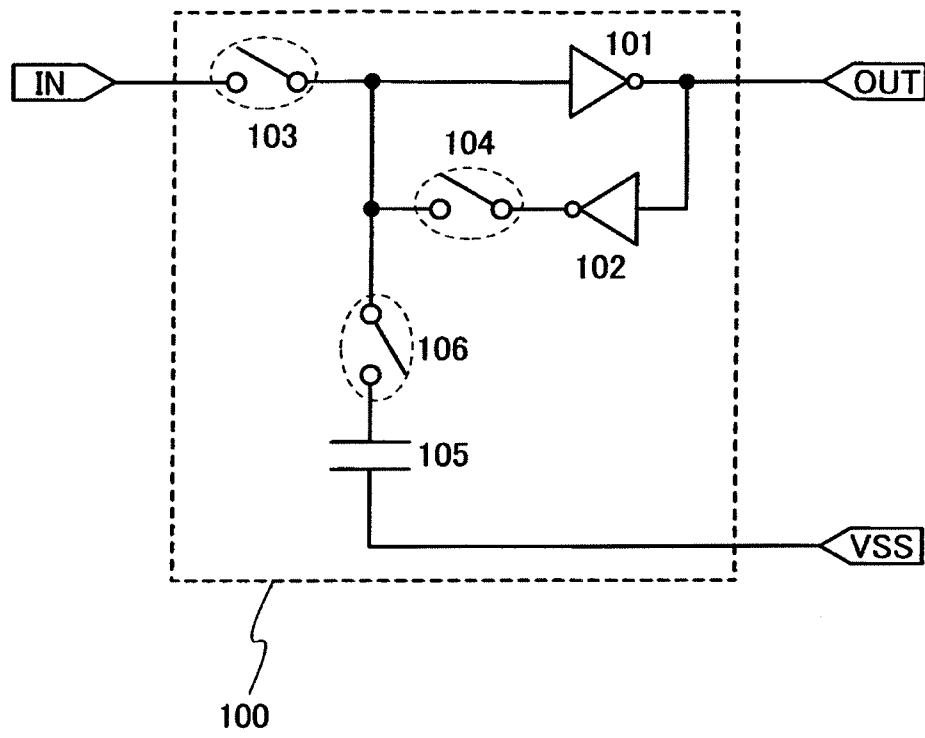


FIG. 2

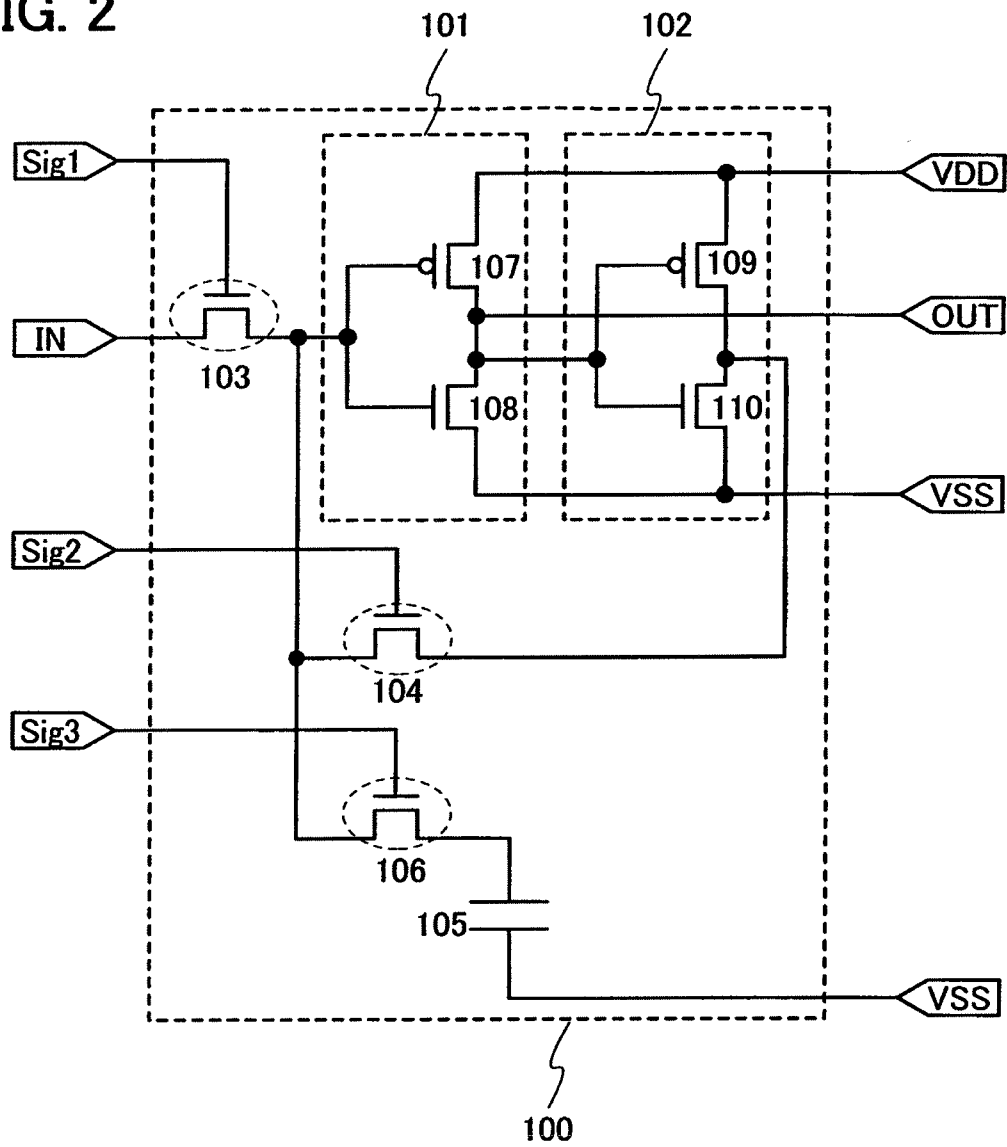


FIG. 3

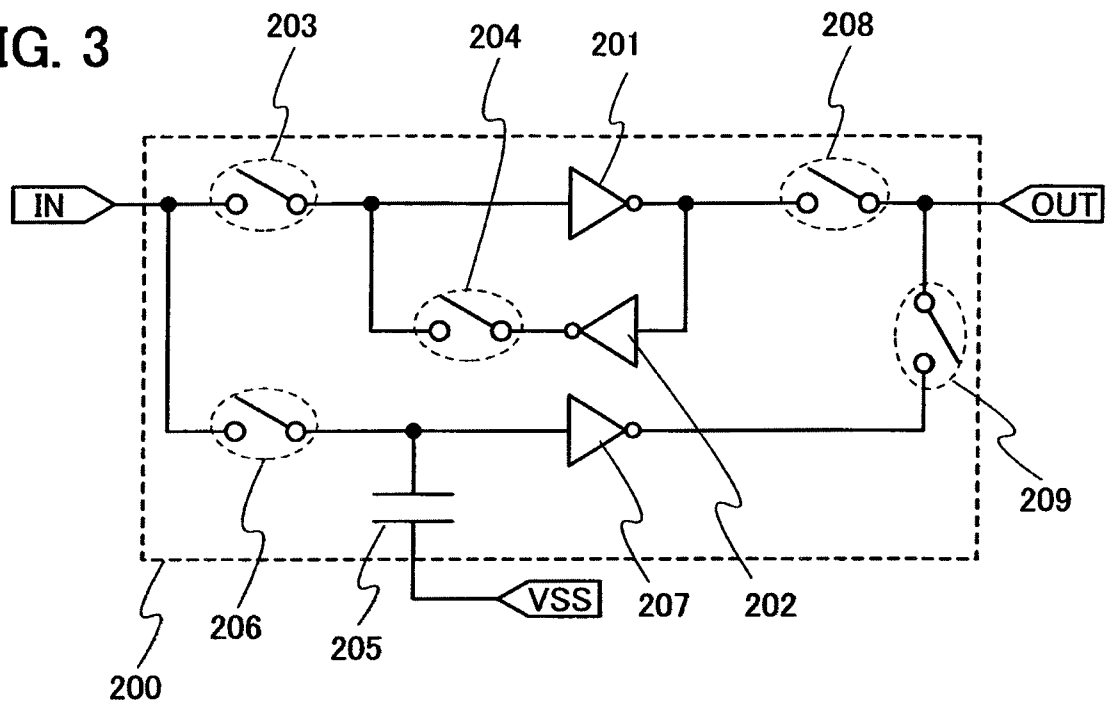


FIG. 4

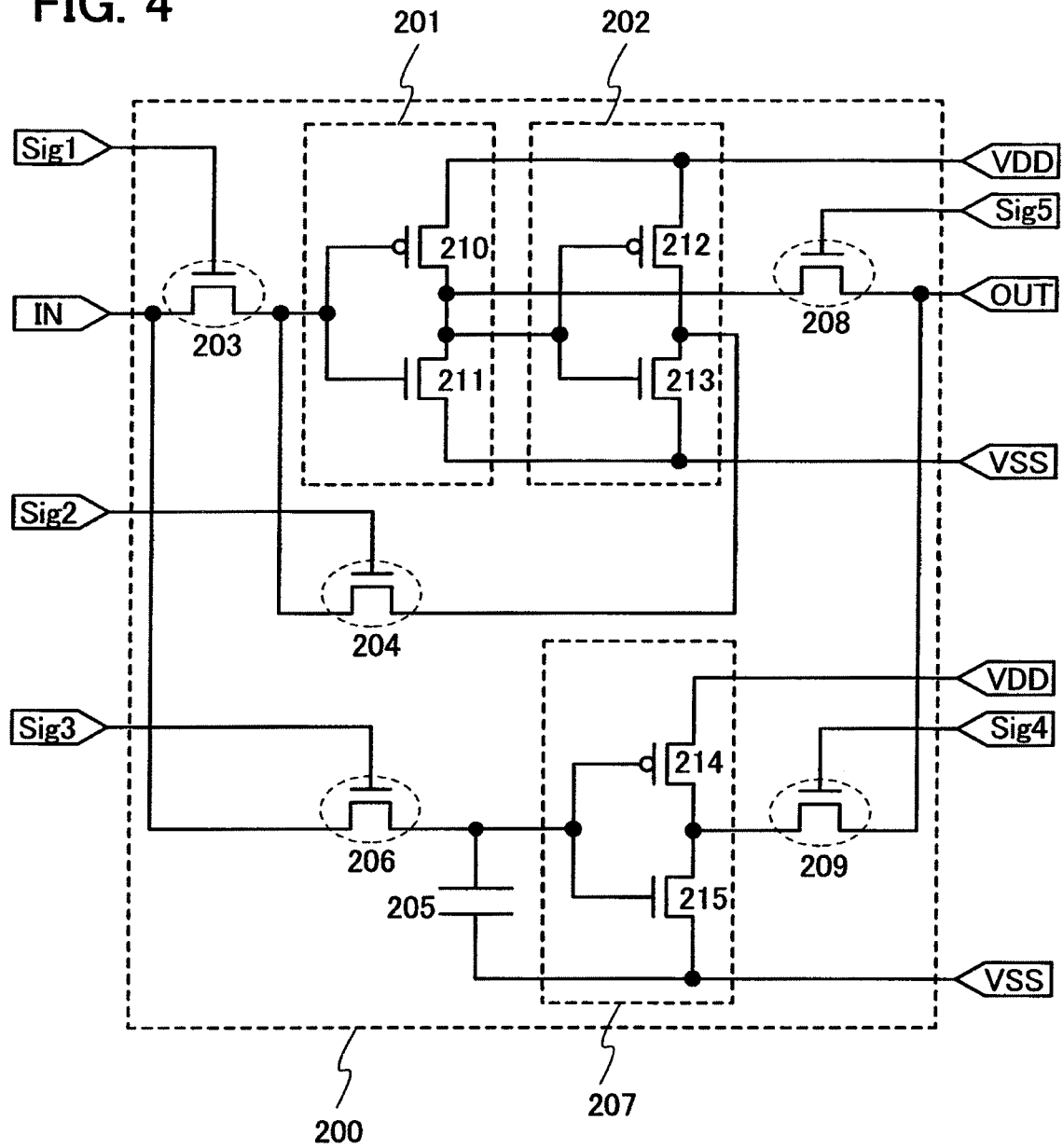


FIG. 5

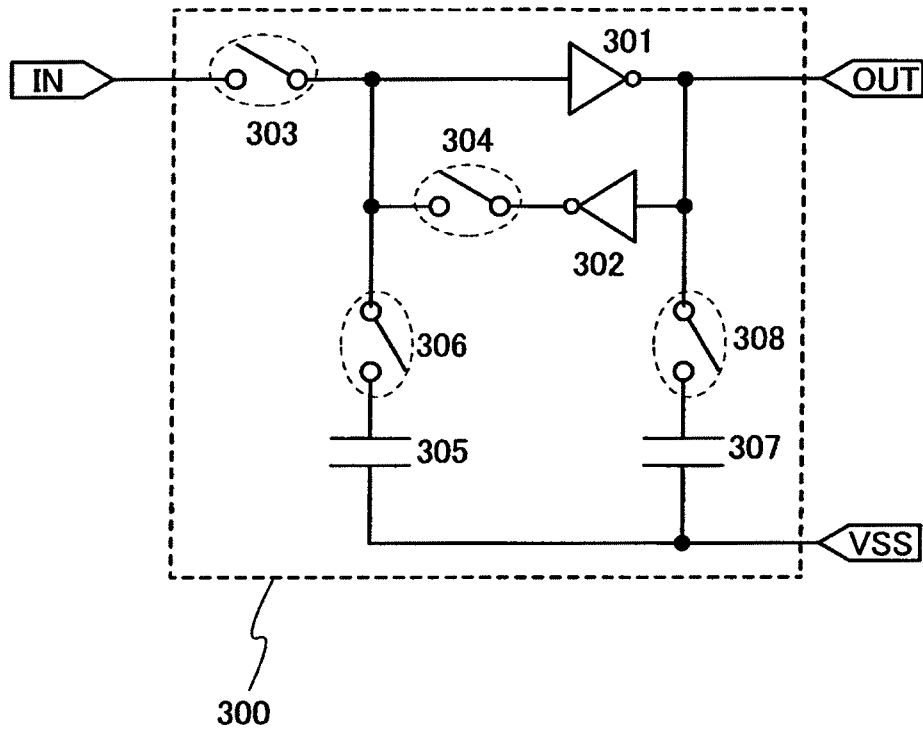


FIG. 6

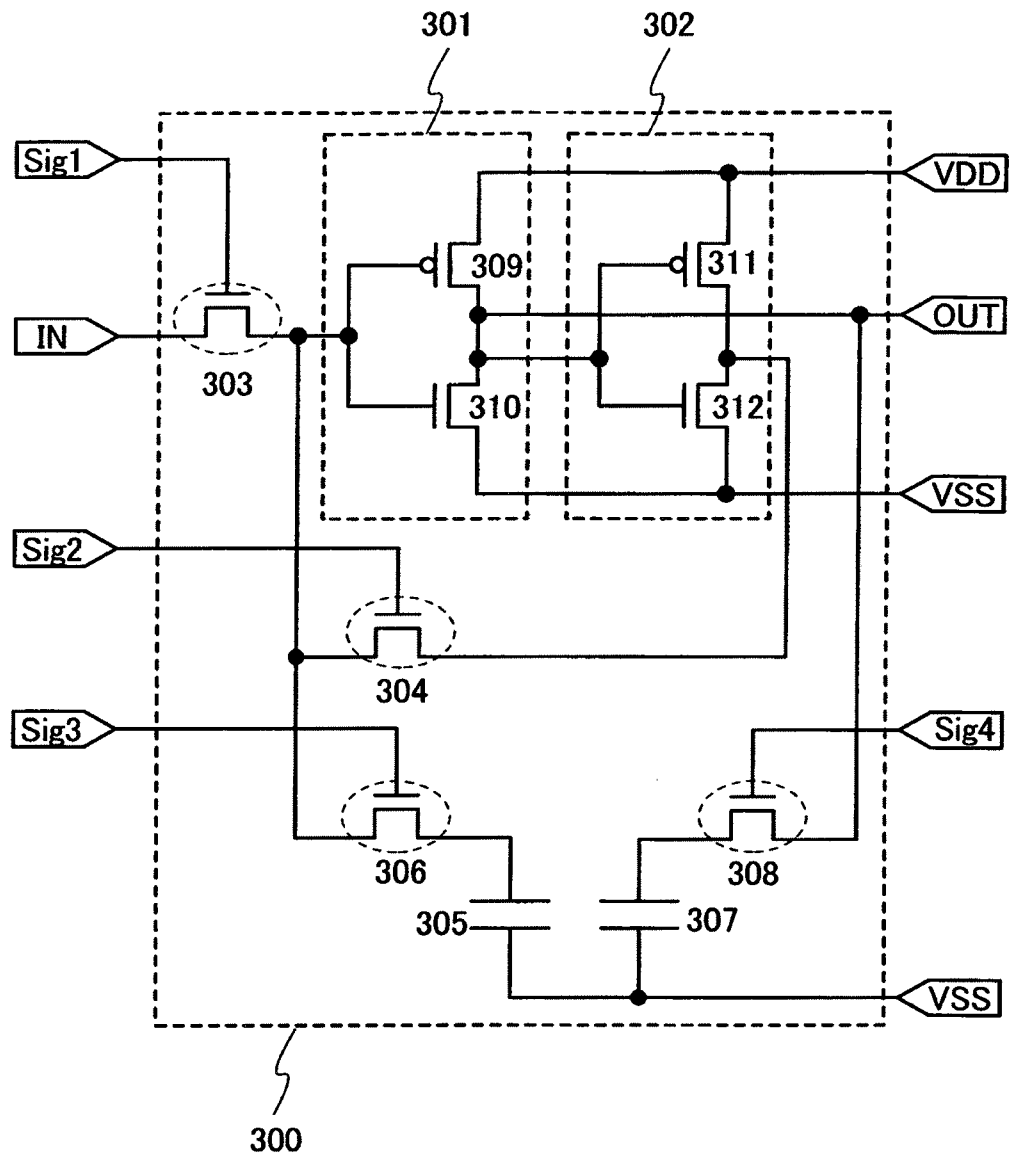


FIG. 7A

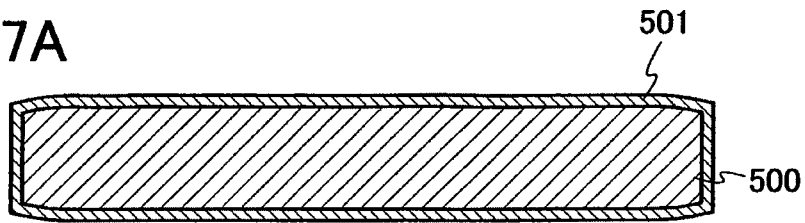


FIG. 7B

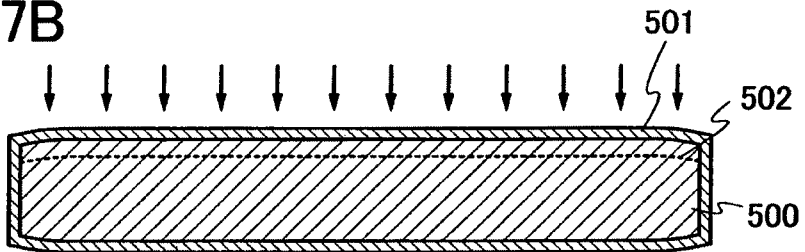


FIG. 7C

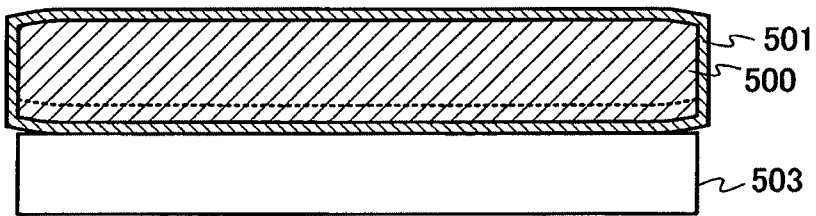


FIG. 7D

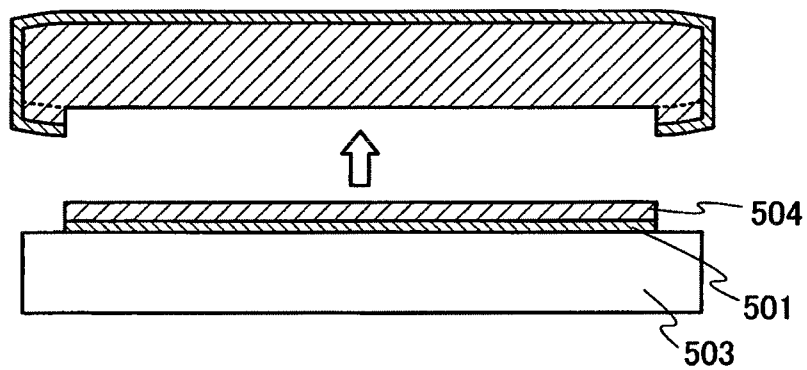


FIG. 7E

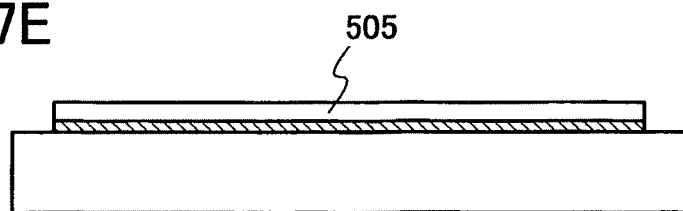


FIG. 8A

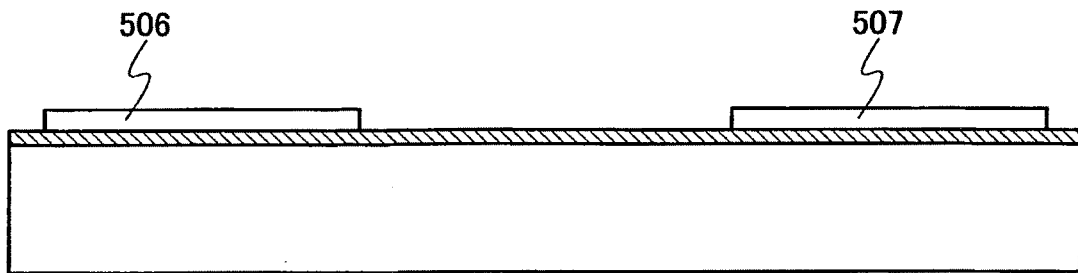


FIG. 8B

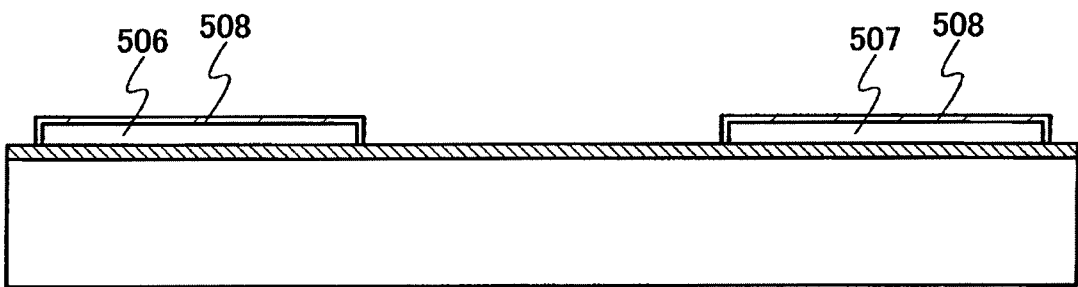


FIG. 8C

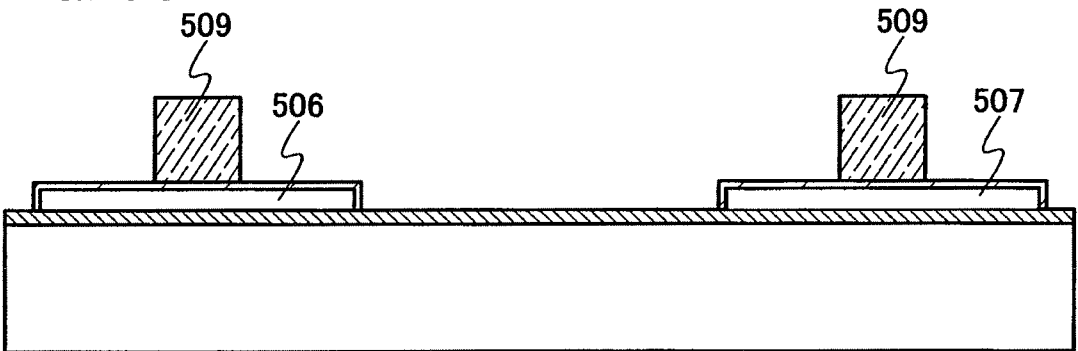


FIG. 8D

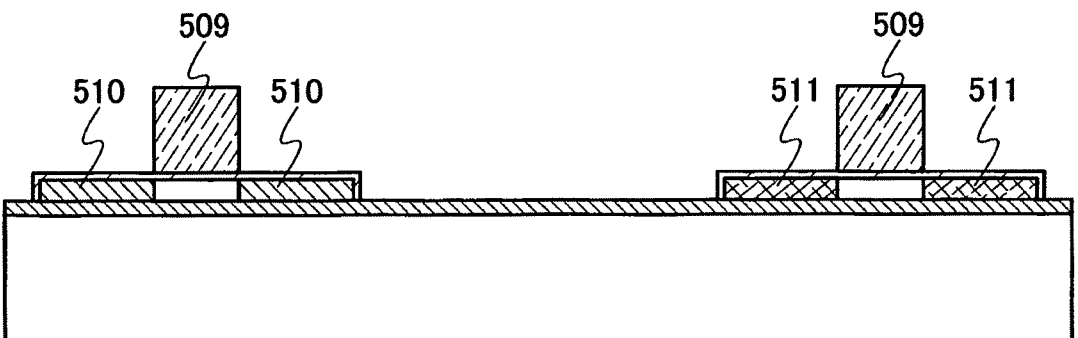


FIG. 9A

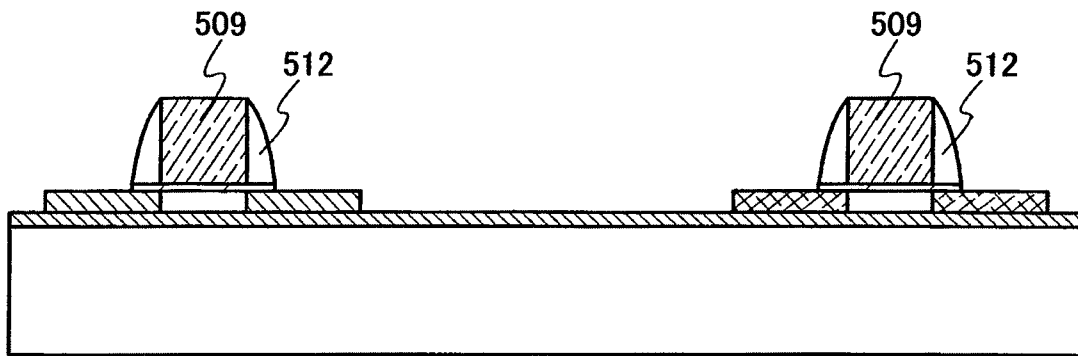


FIG. 9B

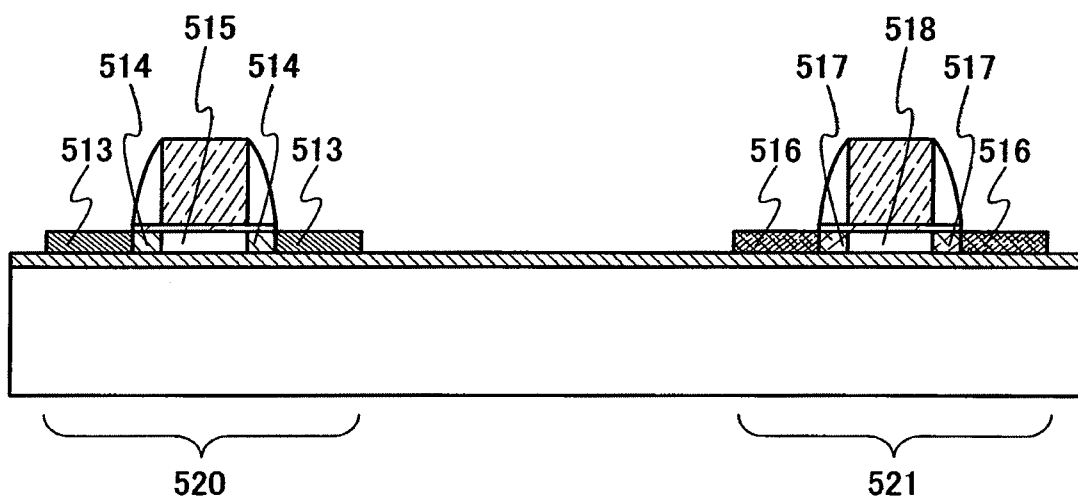


FIG. 10A

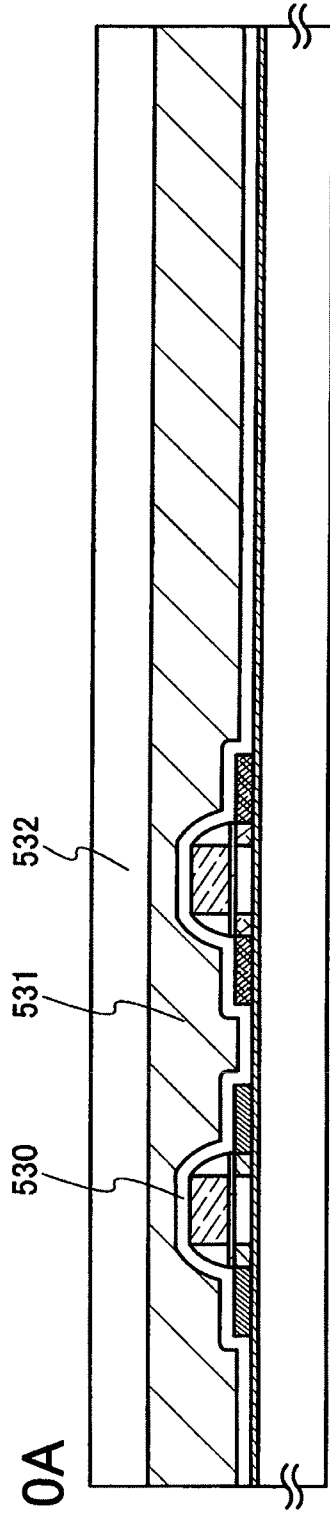


FIG. 10B

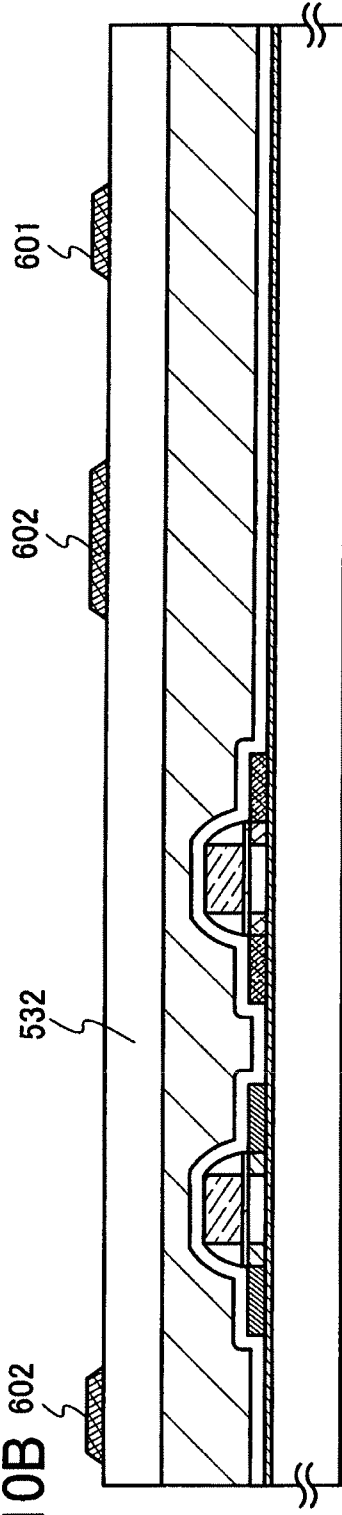
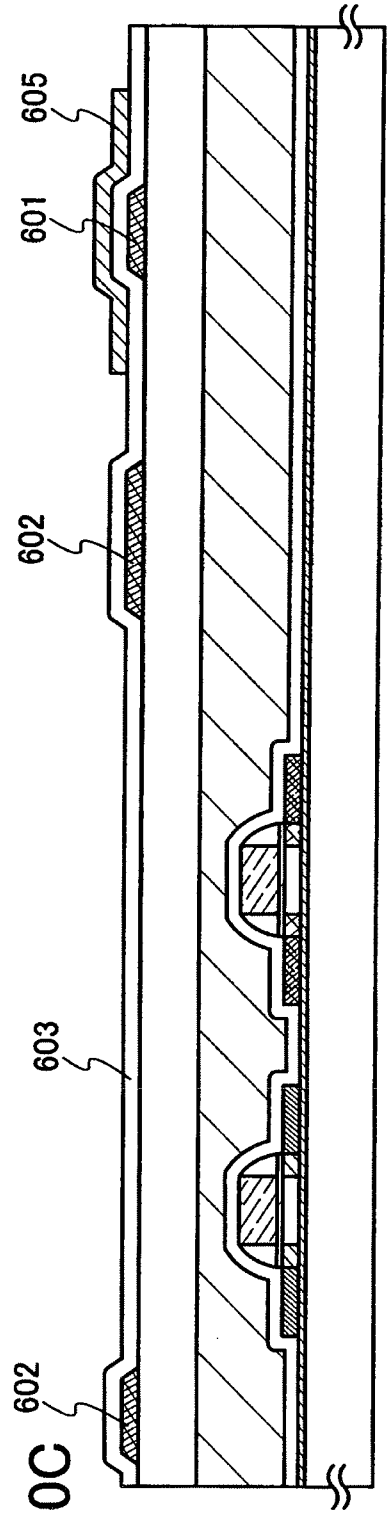


FIG. 10C



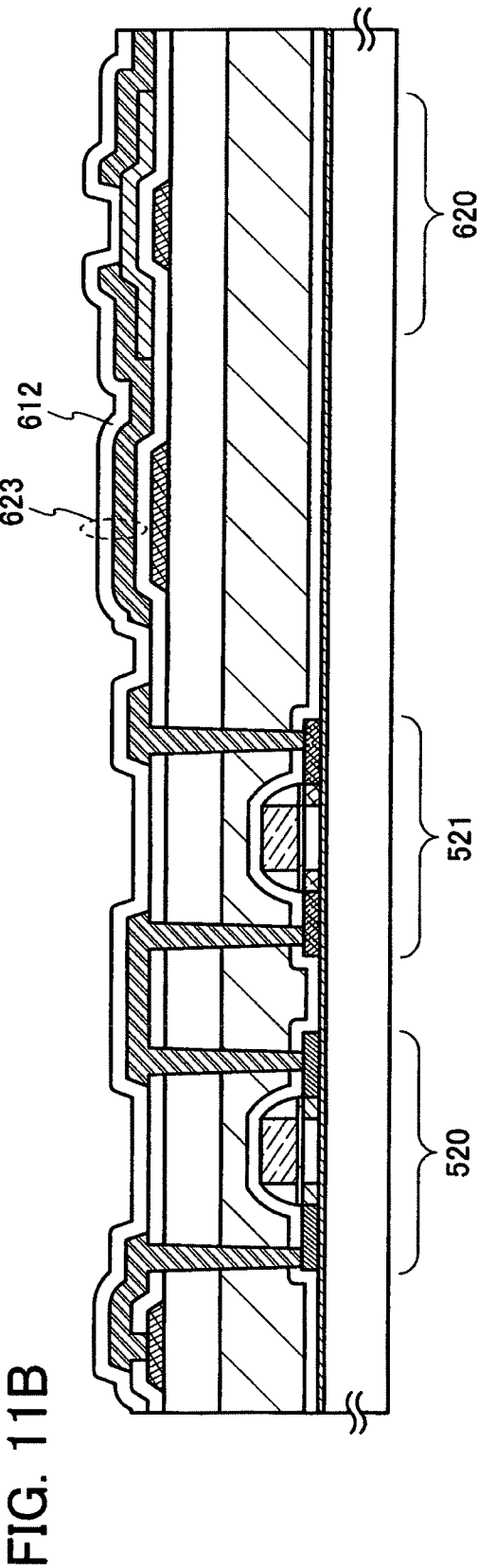
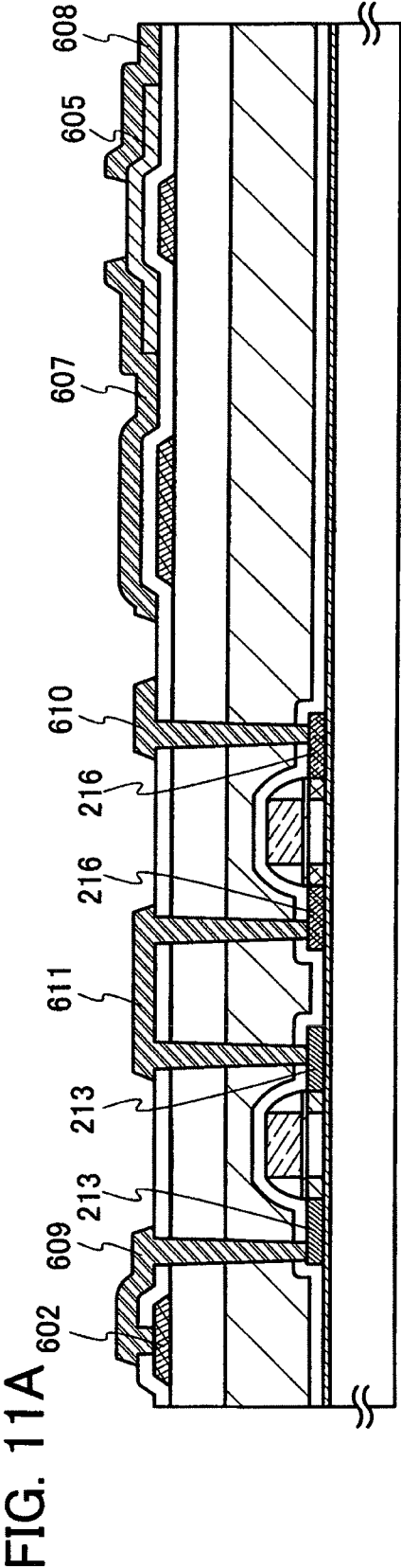


FIG. 12A

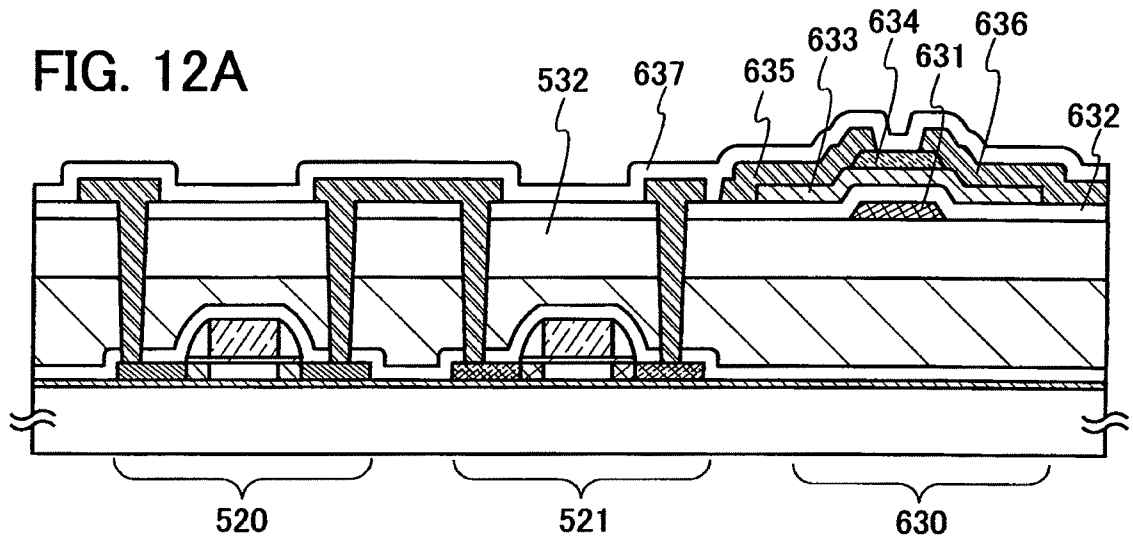


FIG. 12B

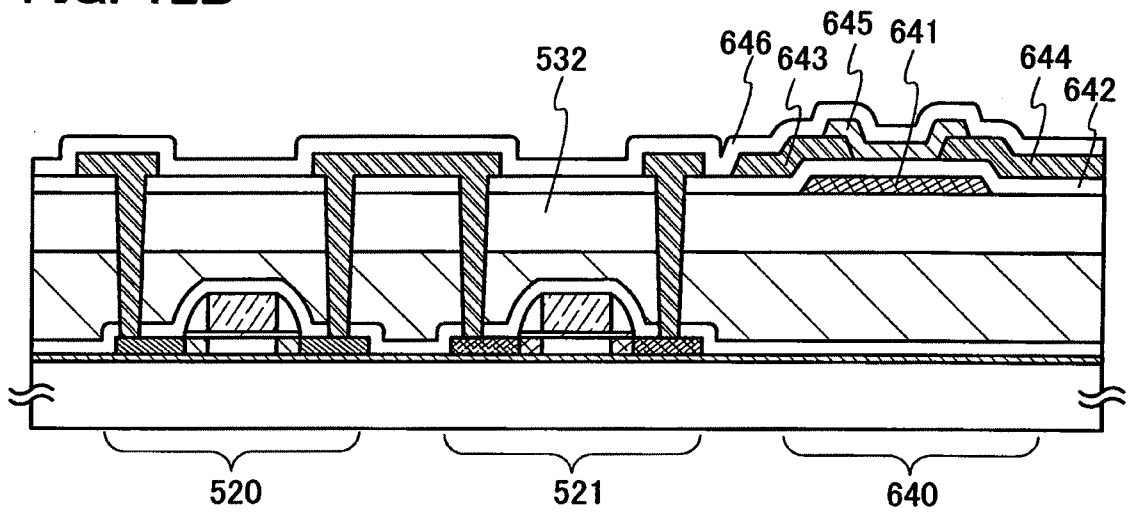


FIG. 12C

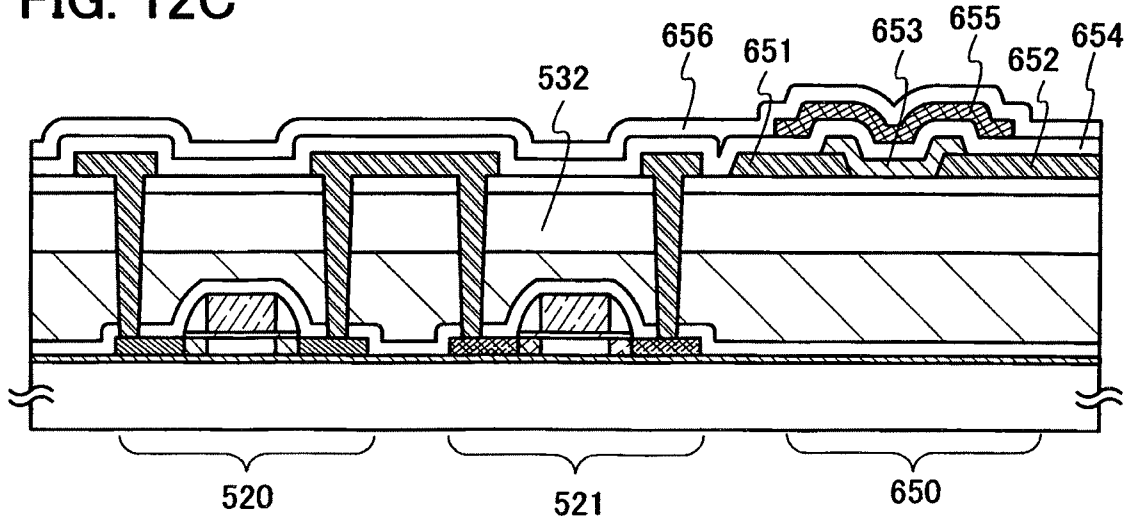


FIG. 14A

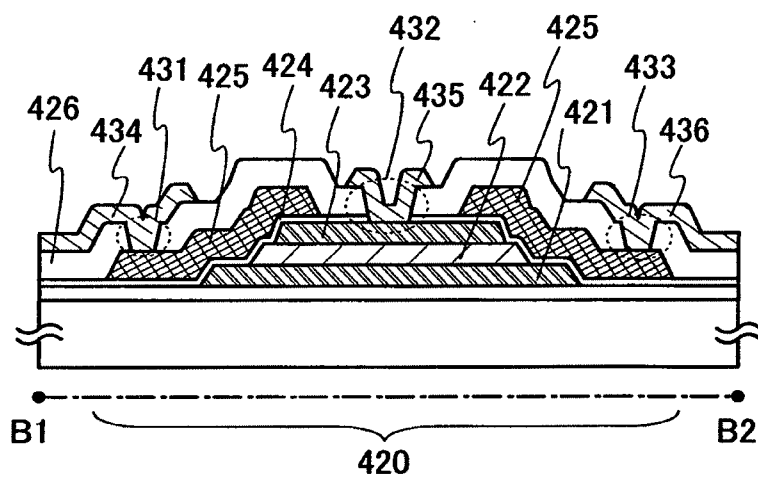


FIG. 14B

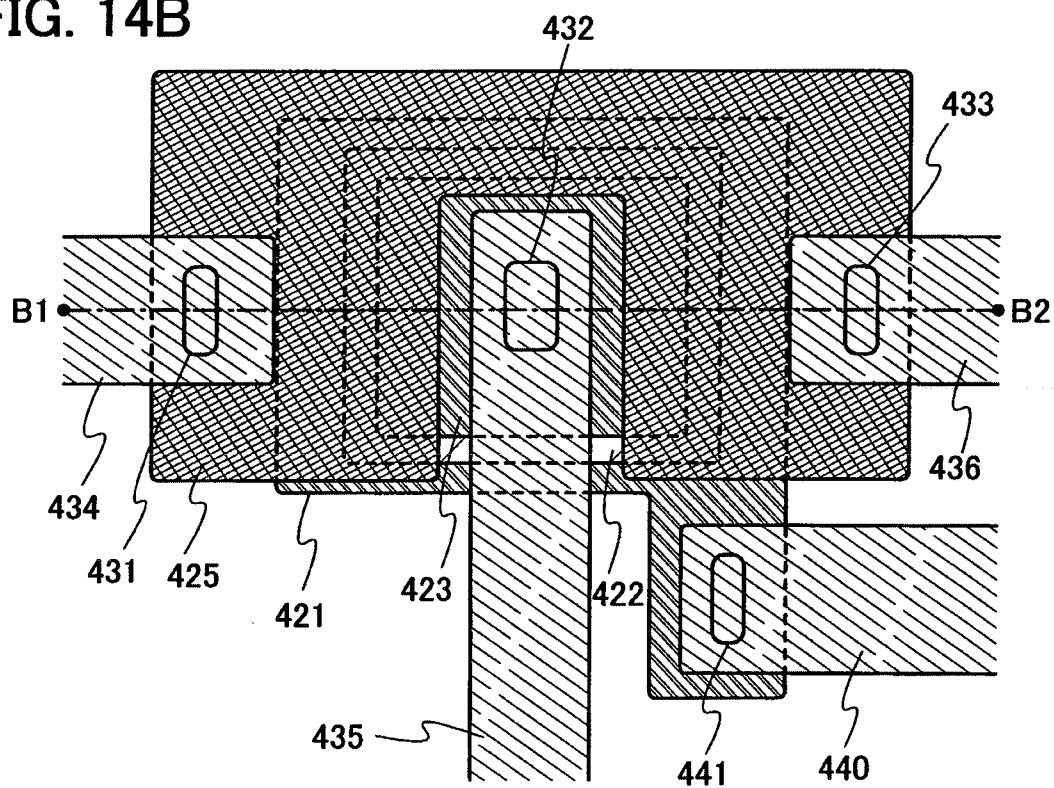


FIG. 15A

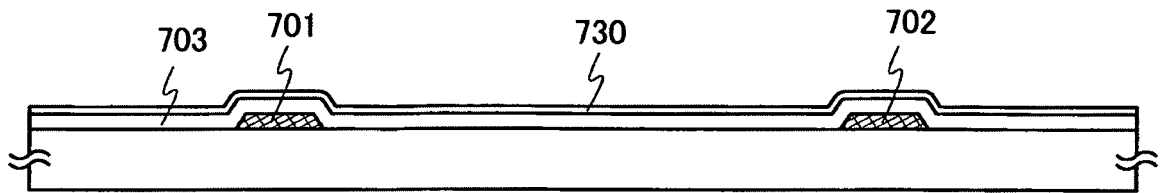


FIG. 15B

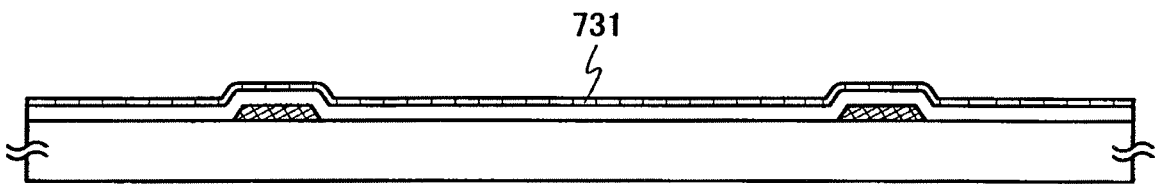


FIG. 15C

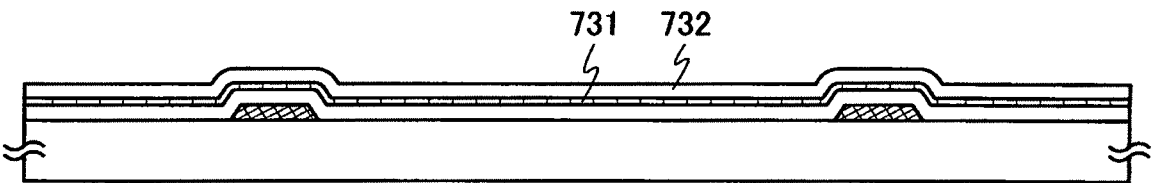


FIG. 15D

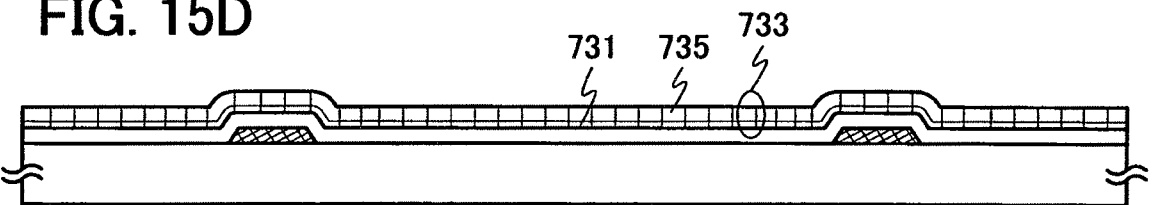


FIG. 15E

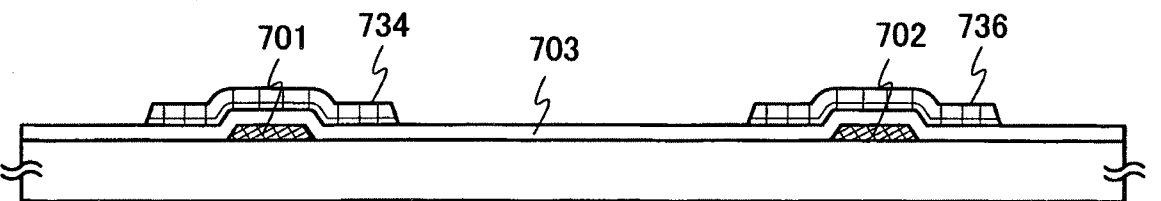


FIG. 16A

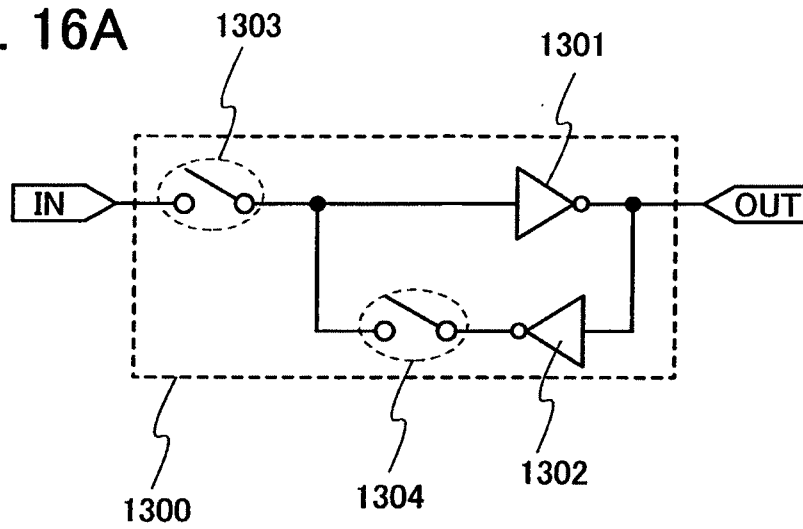


FIG. 16B

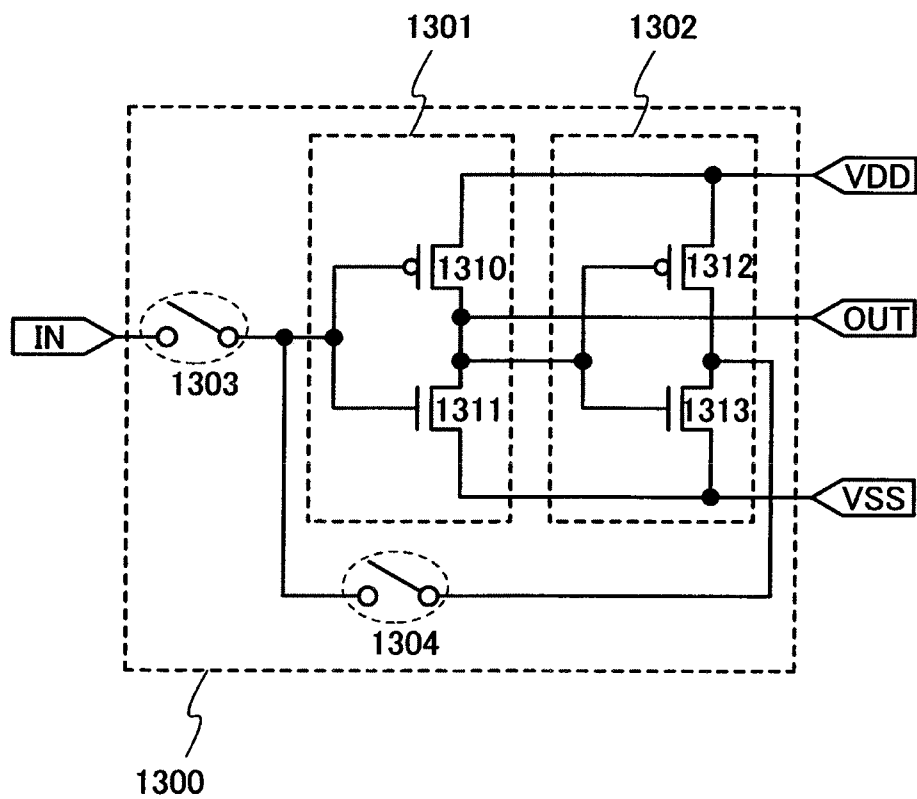


FIG. 17

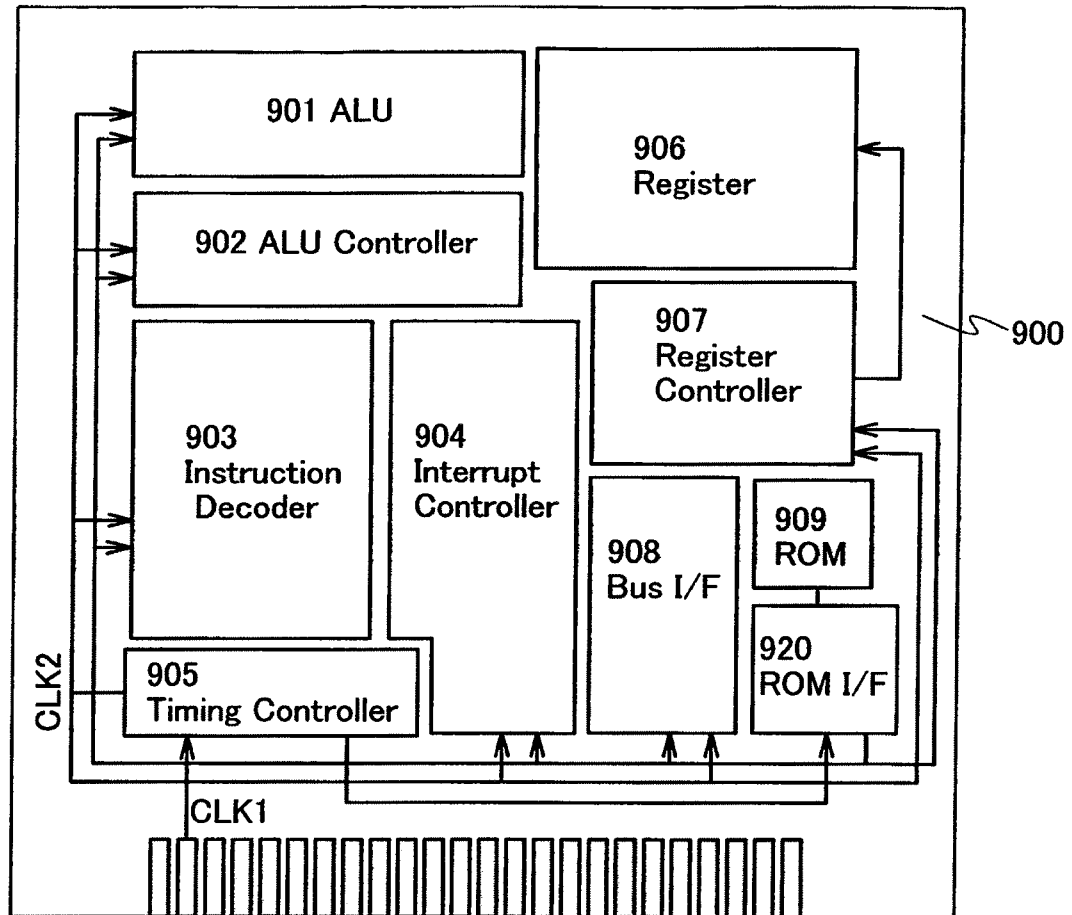


FIG. 18A

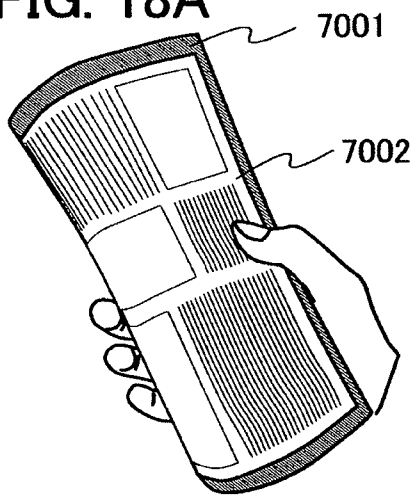


FIG. 18B

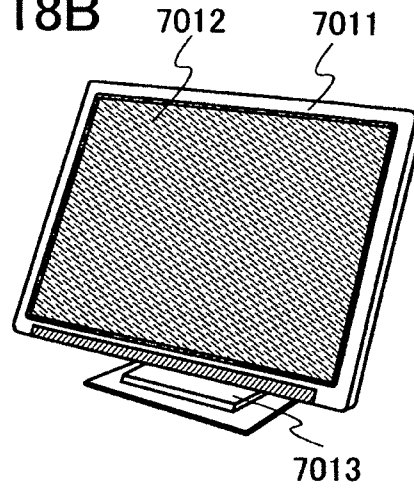


FIG. 18C

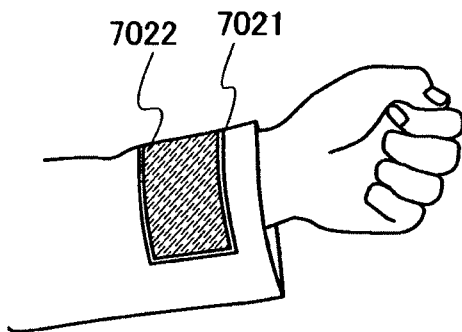


FIG. 18D

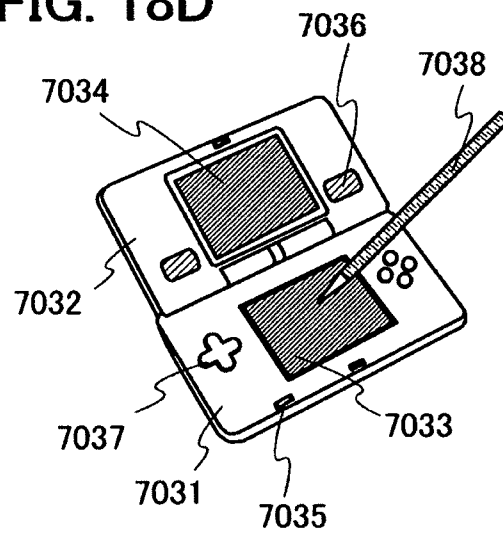


FIG. 18E

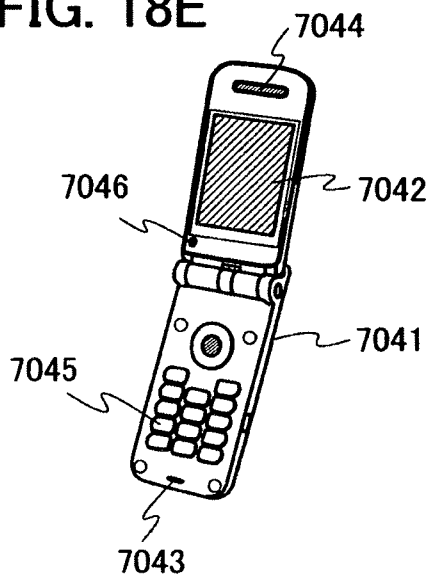


FIG. 18F

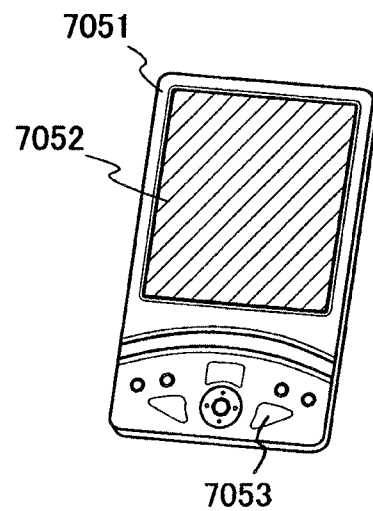


FIG. 19

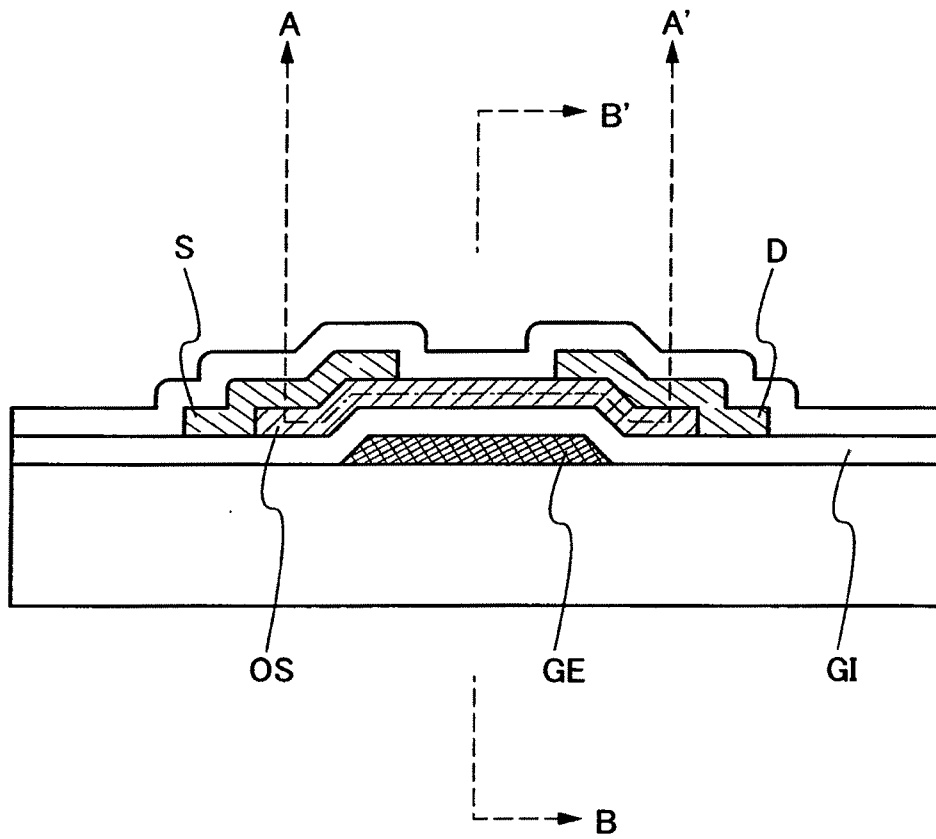


FIG. 20

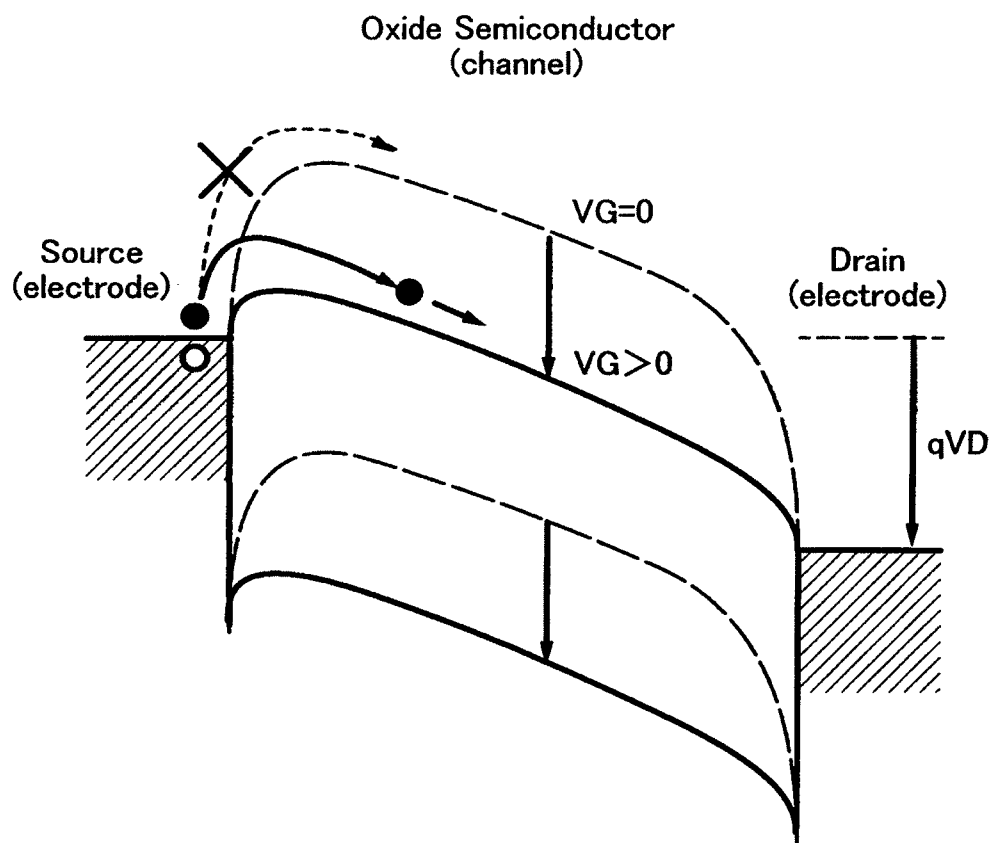
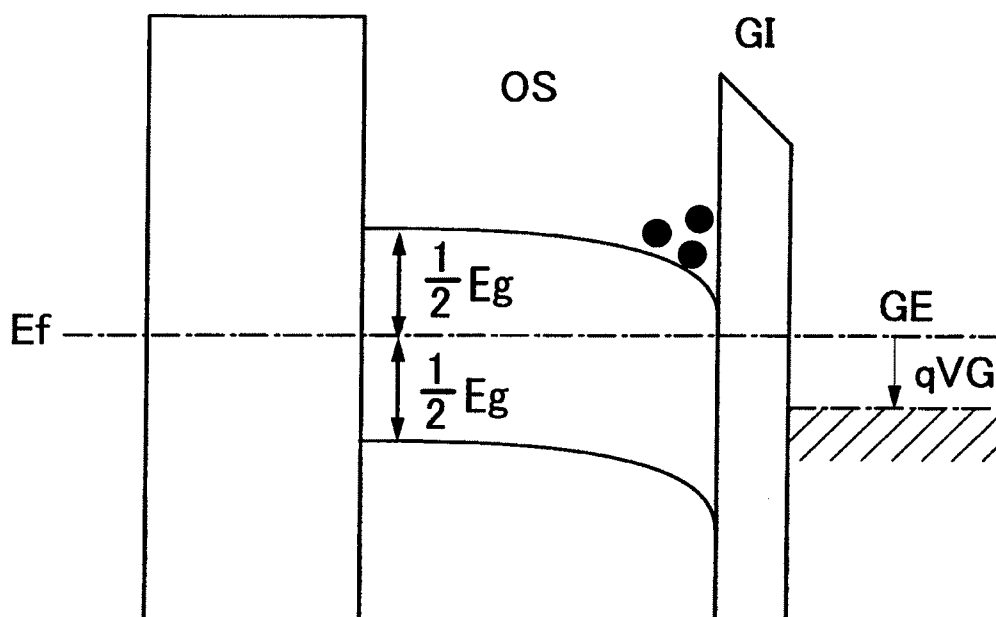
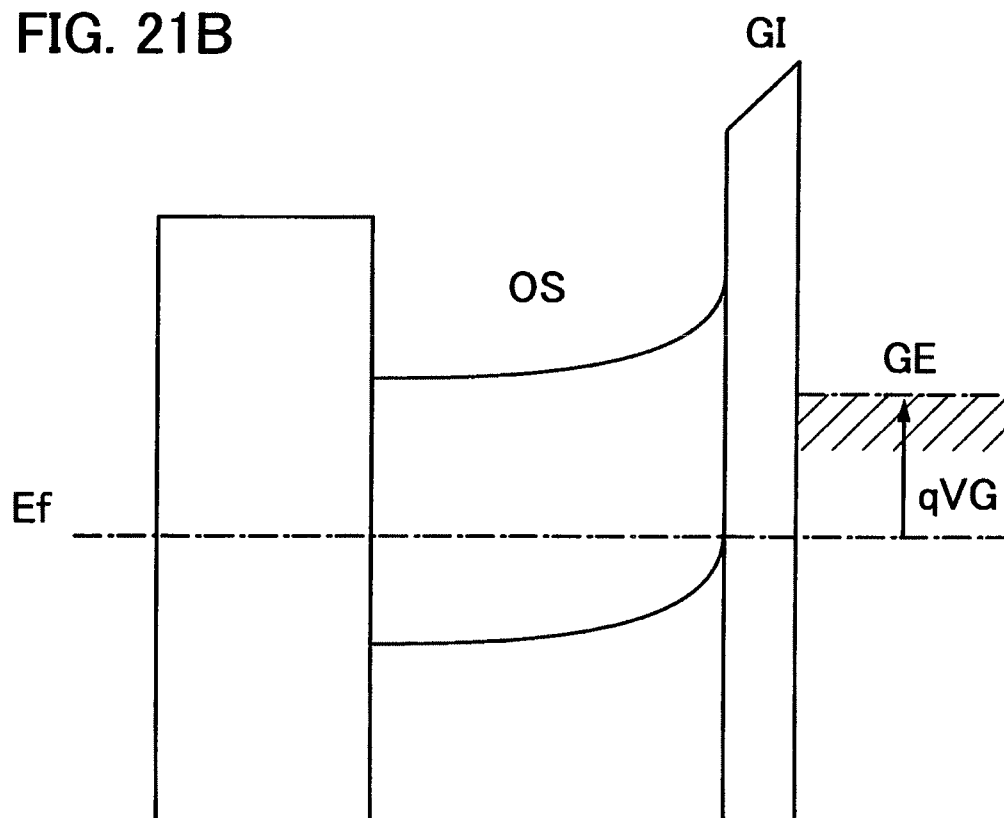


FIG. 21A



(VG>0)

FIG. 21B



(VG < 0)

FIG. 22

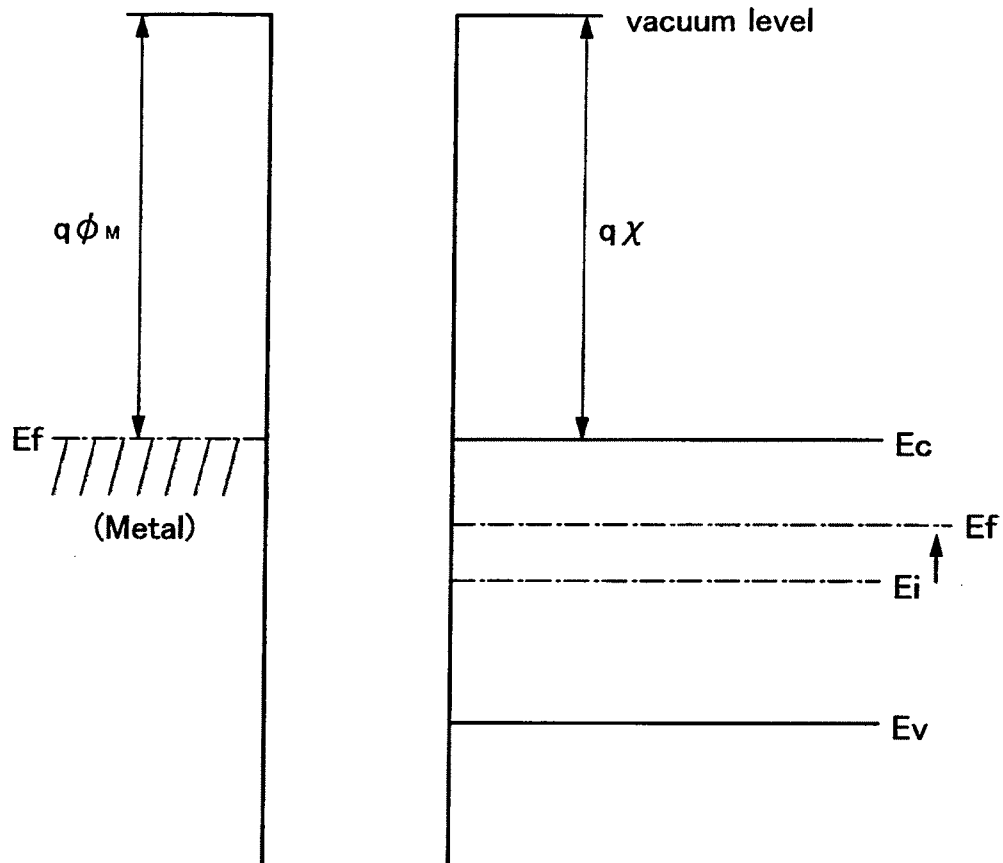


FIG. 23

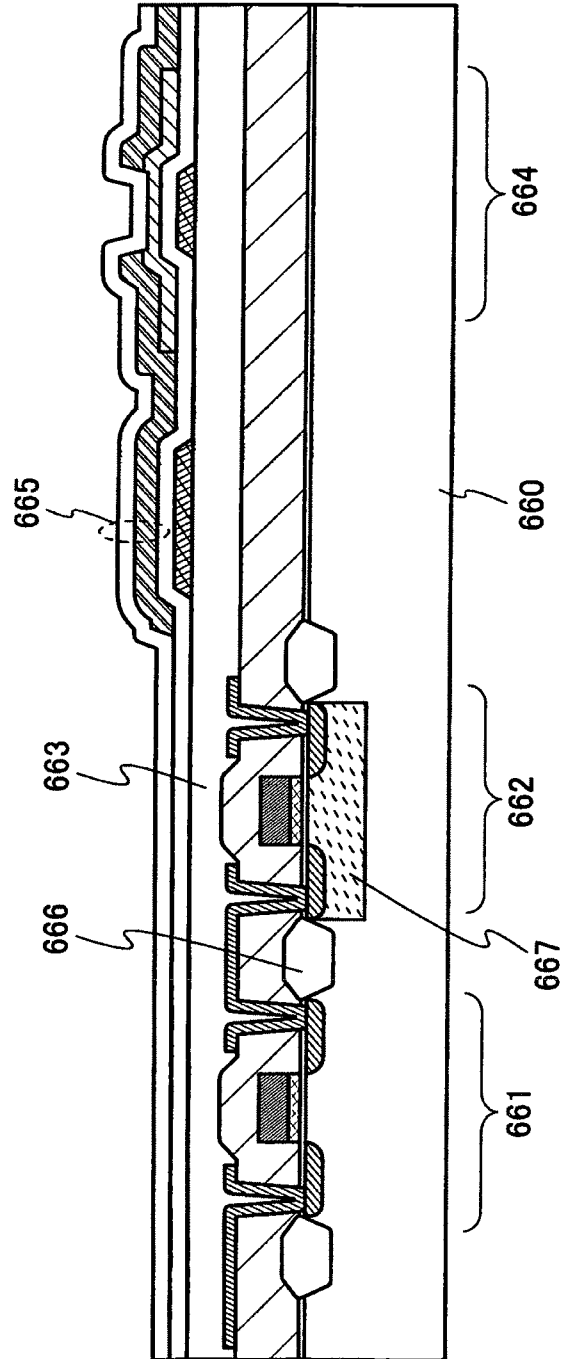


FIG. 24

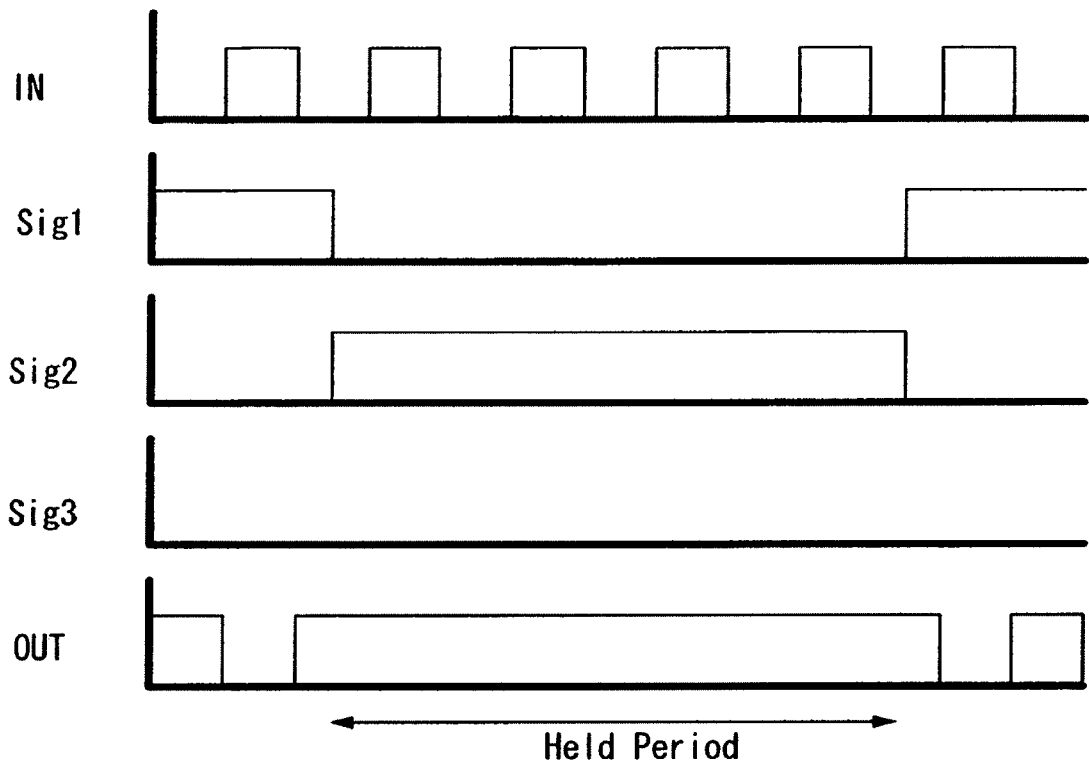


FIG. 25

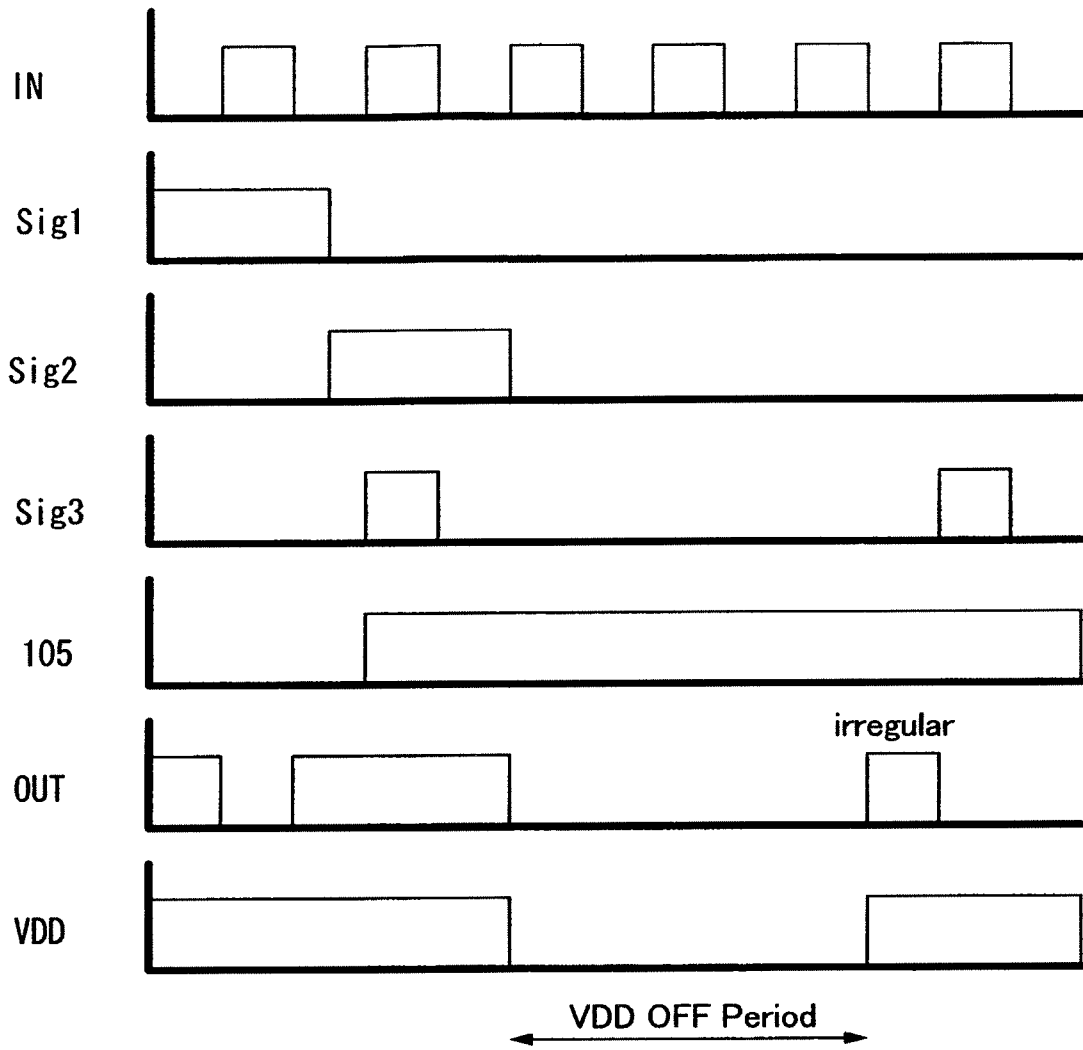


FIG. 26

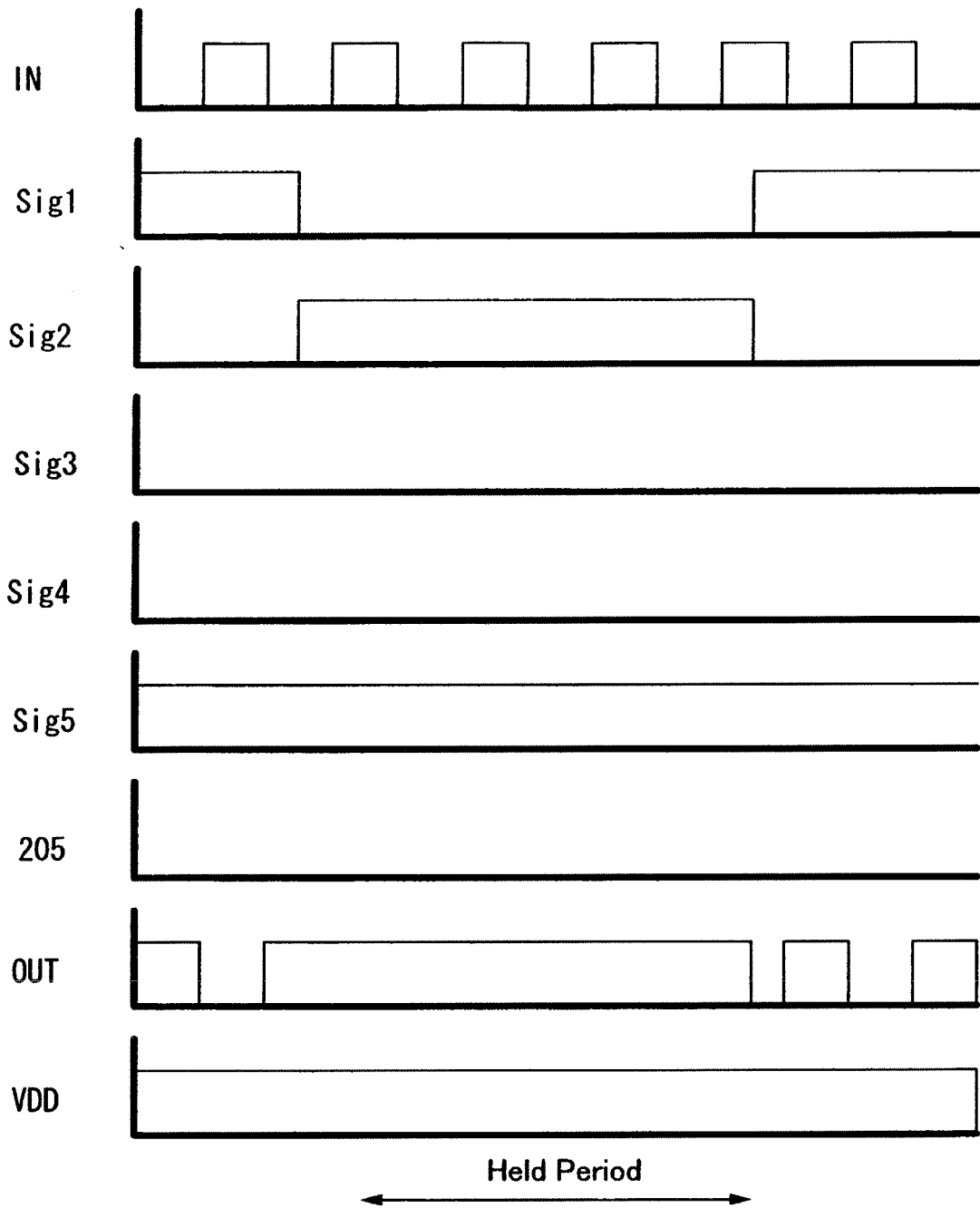


FIG. 27

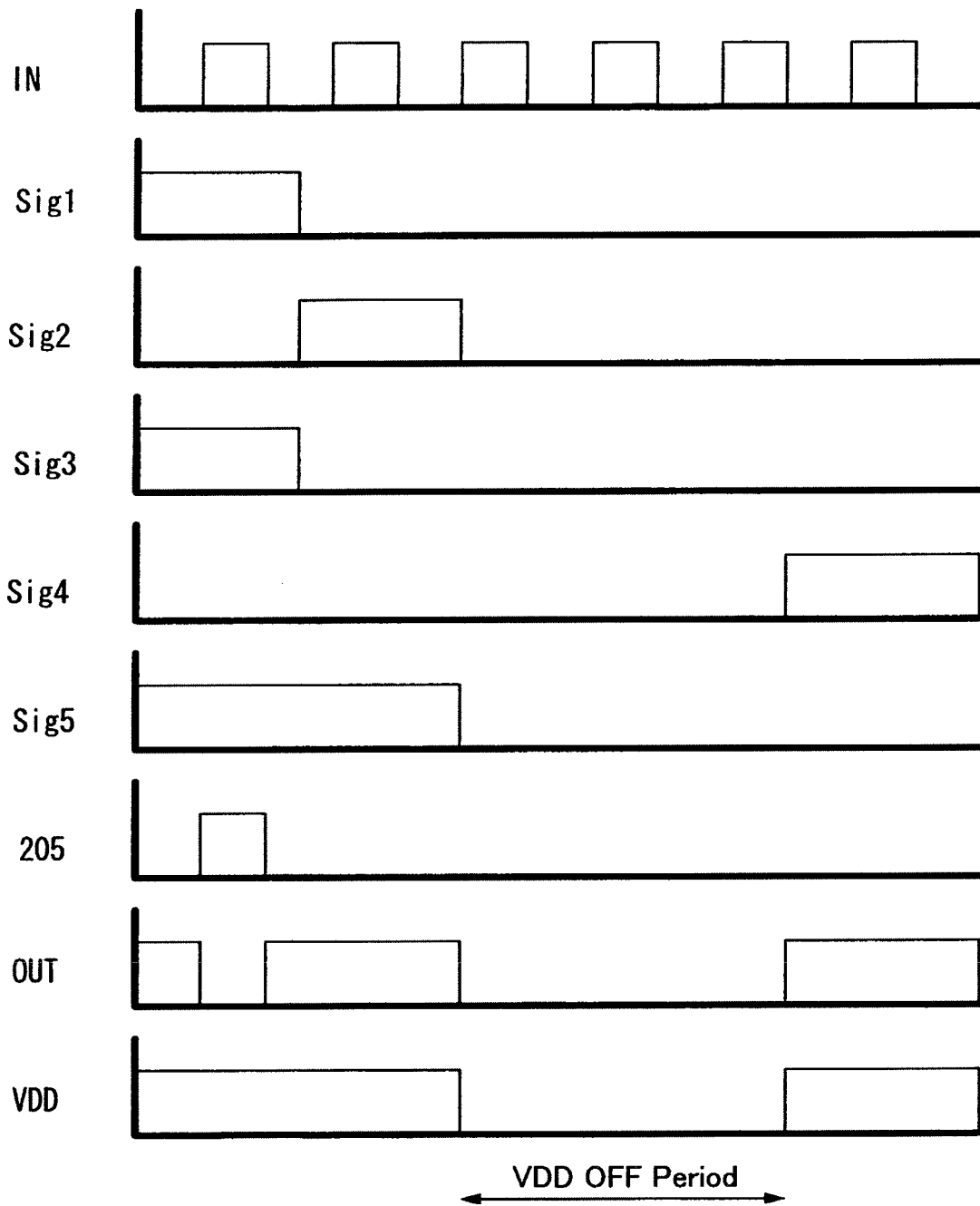


FIG. 28

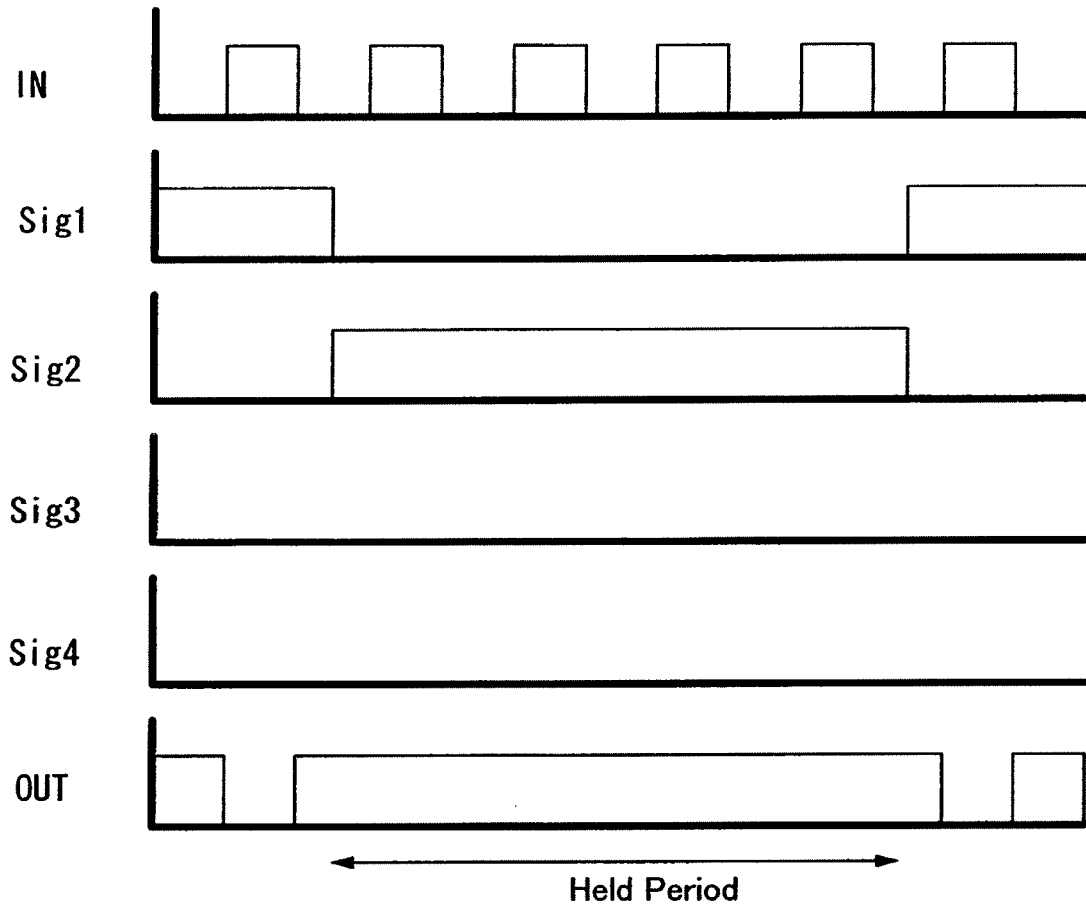
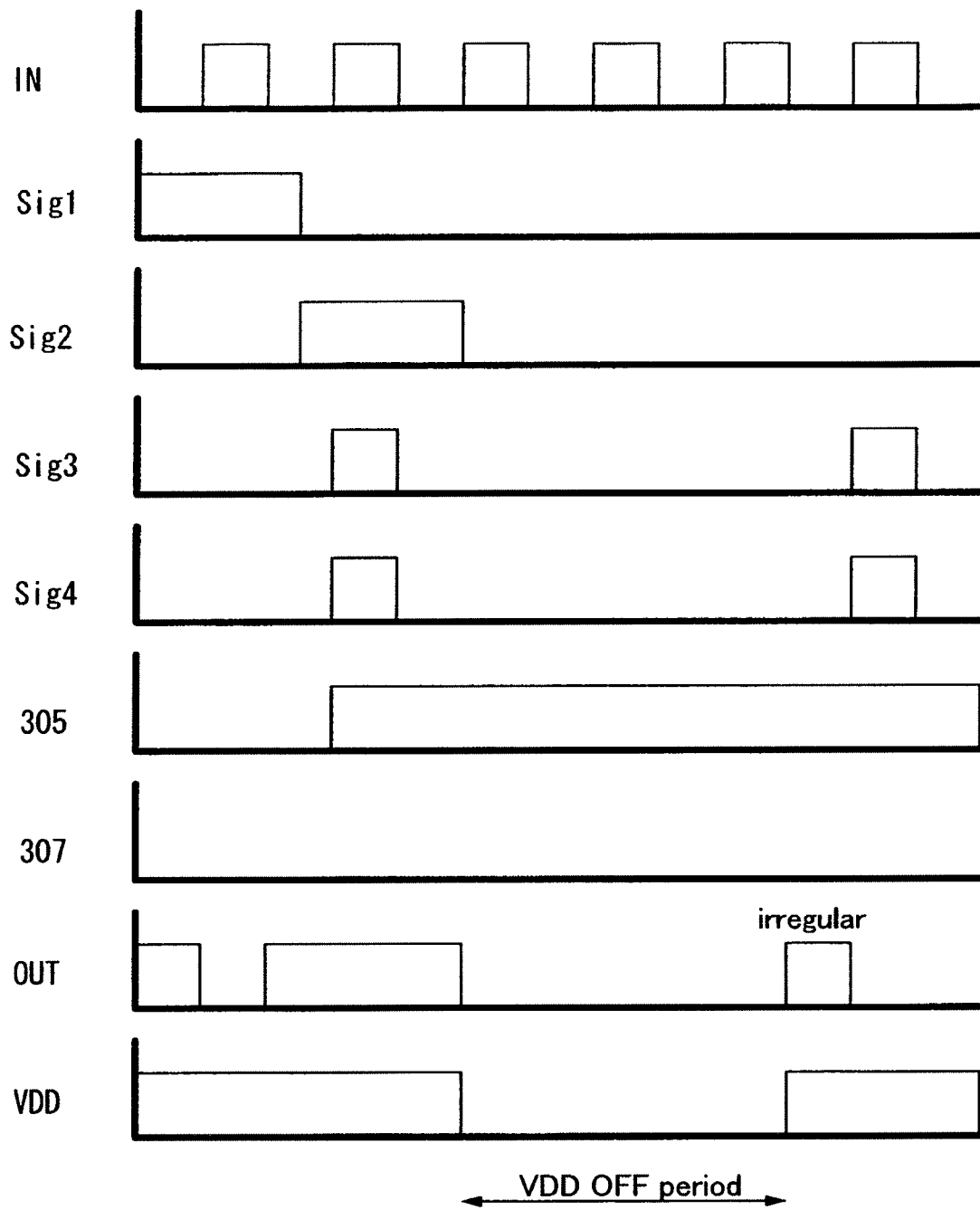


FIG. 29



EXPLANATION OF REFERENCE

100: memory element, 101: phase-inversion element, 102:
 phase-inversion element, 103: switching element, 104: switching element,
 5 105: capacitor, 106: capacitor switching element, 107: p-channel
 transistor, 108: n-channel transistor, 109: p-channel transistor, 110:
 n-channel transistor, 200: memory element, 201: phase-inversion element,
 202: phase-inversion element, 203: switching element, 204: switching
 element, 205: capacitor, 206: capacitor switching element, 207:
 10 phase-inversion element, 208: switching element, 209: switching element,
 210: p-channel transistor, 211: n-channel transistor, 212: p-channel
 transistor, 213: n-channel transistor, 214: p-channel transistor, 215:
 n-channel transistor, 300: memory element, 301: phase-inversion element,
 302: phase-inversion element, 303: switching element, 304: switching
 15 element, 305: capacitor, 306: capacitor switching element, 307: capacitor,
 308: capacitor switching element, 309: p-channel transistor, 310:
 n-channel transistor, 311: p-channel transistor, 312: n-channel transistor,
 401: switching element, 402: memory element, 403: memory element
 group, 420: transistor, 421: first electrode, 422: oxide semiconductor film,
 20 423: second electrode, 424: gate insulating film, 425: gate electrode, 426:
 insulating film, 431: contact hole, 432: contact hole, 433: contact hole,
 434: wiring, 435: wiring, 436: wiring, 440: wiring, 441: contact hole, 500:
 bond substrate, 501: insulating film, 502: embrittlement layer, 503: base
 substrate, 504: semiconductor film, 505: semiconductor film, 506:

semiconductor film, 507: semiconductor film, 508: gate insulating film, 509: electrode, 510: impurity region, 511: impurity region, 512: side wall, 513: high-concentration impurity region, 514: low-concentration impurity region, 515: channel formation region, 516: high-concentration impurity region, 517: low-concentration impurity region, 518: channel formation region, 520: n-channel transistor, 521: p-channel transistor, 530: insulating film, 531: insulating film, 532: insulating film, 601: gate electrode, 602: electrode, 603: gate insulating film, 605: oxide semiconductor film, 607: source electrode, 608: drain electrode, 609: wiring, 610: wiring, 611: wiring, 612: insulating film, 620: transistor, 623: capacitor, 630: transistor, 631: gate electrode, 632: gate insulating film, 633: oxide semiconductor film, 634: channel protective film, 635: source electrode, 636: drain electrode, 637: insulating film, 640: transistor, 641: gate electrode, 642: gate insulating film, 643: source electrode, 644: drain electrode, 645: oxide semiconductor film, 646: insulating film, 650: transistor, 651: source electrode, 652: drain electrode, 653: oxide semiconductor film, 654: gate insulating film, 655: gate electrode, 656: insulating film, 660: semiconductor substrate, 661: n-channel transistor, 662: p-channel transistor, 663: insulating film, 664: transistor, 665: capacitor, 666: element isolation insulating film, 701: gate electrode, 702: gate electrode, 703: gate insulating film, 730: oxide semiconductor film, 731: oxide semiconductor film, 732: oxide semiconductor film, 733: oxide semiconductor film, 734: oxide semiconductor film, 735: oxide semiconductor film, 736: oxide semiconductor film, 900: substrate, 901:

ALU, 902: ALU controller, 903: instruction decoder, 904: interrupt controller, 905: timing controller, 906: register, 907: register controller, 908: bus I/F, 909: ROM, 920: ROM I/F, 1300: register, 1301: inverter, 1302: inverter, 1303: switching element, 1304: switching element, 1310: 5 p-channel transistor, 1311: n-channel transistor, 1312: p-channel transistor, 1313: n-channel transistor, 7001: housing, 7002: display portion, 7011: housing, 7012: display portion, 7013: supporting base, 7021: housing, 7022: display portion, 7031: housing, 7032: housing, 7033: display portion, 7034: display portion, 7035: microphone, 7036: speaker, 7037: operation 10 key, 7038: stylus, 7041: housing, 7042: display portion, 7043: audio-input portion, 7044: audio-output portion, 7045: operation key, 7046: light-receiving portion, 7051: housing, 7052: display portion, 7053: operation key.